

Applicant: Toshiki Makimoto, et al.
 Serial No.: 10/516,380
 Filing Date: November 30, 2004
 For: P-TYPE NITRIDE SEMICONDUCTOR STRUCTURE AND BIPOLAR TRANSISTOR

Confirmation No.: 2860
 Att'y Docket No.: 14321.63
 Art Unit: 2818

INFORMATION DISCLOSURE CITATIONS MADE BY APPLICANT

U.S. Patent Documents

<u>Examiner Initial*</u>	<u>Document Number</u>	<u>Issue Date</u>	<u>Name</u>
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Foreign Patent Documents

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Other Documents

(including author, title, pertinent pages, etc.)

Examiner
Initial*

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| _____ 1 | T. Makimoto, et al., <i>High Current Gains Obtained by InGaN/GaN Double Heterojunction Bipolar Transistors with P-InGaN Base</i> , Applied Physics Letters, 79, No. 3, pp. 380-381, July 16, 2001. |
| _____ 2 | Supplementary European Search Report of related European Application No. 04700296.9, dated April 6, 2009 (2 pages). |

References Cited by Applicants

While the filing of Information Disclosure Statements is voluntary, the procedure is governed by the guidelines of Section 609 of the Manual of Patent Examining Procedure and 37 C.F.R. §§ 1.97 and 1.98. To be considered a proper Information Disclosure Statement, Form PTO-1449 shall be accompanied by a copy of each listed patent or publication or other item of information and a translation of the pertinent portions of foreign documents (if an existing translation is readily available to the applicant), an explanation of relevance of each reference not in the English language, and should be submitted in a timely manner as set out in MPEP Sec. 609.

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The reference designations "A1," "A2," etc. (referring to Applicant's reference 1, Applicant's reference 2, etc.) will be used by the Examiner in the same manner as Examiner's reference designations "A," "B," "C," etc. on Office Action Form PTO-1142.

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